Short Biography of Dr. Benjamin Iñiguez:

Benjamin Iñiguez obtained the Ph D in Physics in 1992 and 1996, respectively, from the Universitat de les Illes Balears (UIB). From February 1997 to September 1998, he was working as a Postdoctoral Researcher at the Rensselaer Polytecnhnic Institute in Troy (NY, USA). From September 1998 to January 2001, he was working as a Postdoctoral Scientist in the Université catholiquede Louvain (Louvain-la-Neuve, Belgium), supported by two Marie Curie Fellowships from the European Commission. In February 2001 he joined the Department of Electronic, Electrical and Automatic Control Engineering (DEEEiA)of the Universitat Rovira i Virgili (URV), in Tarragona, Catalonia, Spain) as Titular Professor. In February 2010 he became Full Professor at URV. He obtained the Distinction from the Generalitat for the Promotion of University Research in 2004 and the ICREA Academia Award (the highest award for university professors in Catalonia, from ICREA Institute) in 2009 and 2014. He led two research projects funded by the European Union (EU) and has participated as URV team leader in four more EU-funded projects.   He has supervised or co-supervised 13 Ph D students. He has been the Chair Person of five international conferences and workshops devoted to advanced semiconductor devices, as well as four international training courses on device modeling.

He is EDS Distinguished Lecturer since 2004, Editor of IEEE T-ED since August 2016, Chair of the EDS Compact Modeling Technical Council since January 2017, EDS BoG Member at Large since January 2018, and SRC Region 8 Vice-Chair since January 2020. In 2019 he was elected IEEE Fellow.

His main research interests are the characterization, parameter extraction and compact modelling of emerging semiconductor devices, in particular nanoscale Multi-Gate MOSFETs GaN HEMTs, and organic and oxide Thin-Film Transistors. He has published more than 180 research papers in international journals and more than 170 abstracts in proceedings of conferences.